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July 2012

FAN7393A
Half-Bridge Gate Drive IC

Features

- Floating Channel for Bootstrap Operation to +600V
- Typically 2.5A/2.5A Sourcing/Sinking Current Driving Capability
- Extended Allowable Negative V_S Swing to -9.8V for Signal Propagation at V_{BS}=15V
- High-Side Output in Phase of IN Input Signal
- 3.3V and 5V Input Logic Compatible
- Matched Propagation Delay for Both Channels
- Built-in Shutdown Function
- Built-in UVLO Functions for Both Channels
- Built-in Common-Mode dv/dt Noise Cancelling Circuit
- Internal 400ns Minimum Dead Time at R_{DT}=0Ω
- Programmable Turn-On Delay Control (Dead-Time)

Applications

- High-Speed Power MOSFET and IGBT Gate Driver
- Induction Heating
- High-Power DC-DC Converter
- Synchronous Step-Down Converter
- Motor Drive Inverter

Description

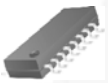
The FAN7393A is a half-bridge gate-drive IC with shut-down and programmable dead-time control functions that can drive high-speed MOSFETs and Isolated Gate Bridge Transistors (IGBTs) operating up to +600V. It has a buffered output stage with all NMOS transistors designed for high-pulse-current driving capability and minimum cross-conduction.

Fairchild's high-voltage process and common-mode noise canceling techniques provide stable operation of the high-side driver under high dv/dt noise circum-stances. An advanced level-shift circuit offers high-side gate driver operation up to V_S=-9.8V (typical) for V_{BS}=15V.

The UVLO circuit prevents malfunction when V_{DD} and V_{BS} are lower than the specified threshold voltage.

The high-current and low-output voltage drop feature makes this device suitable for diverse half- and full-bridge inverters; motor drive inverters, switching mode power supplies, induction heating, and high-power DC-DC converter applications.

14-SOP



Ordering Information

Part Number	Package	Operating Temperature	Packing Method
FAN7393AMX	14-SOIC	-40°C to +125°C	Tape & Reel

Typical Application Diagrams

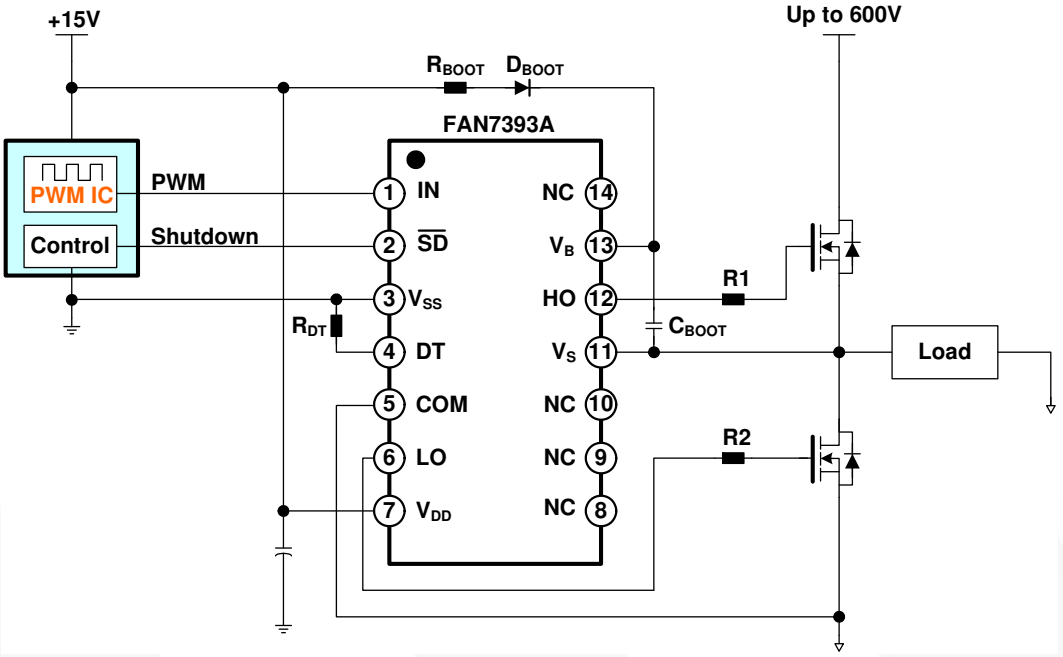


Figure 1. Typical Application Circuit

Internal Block Diagram

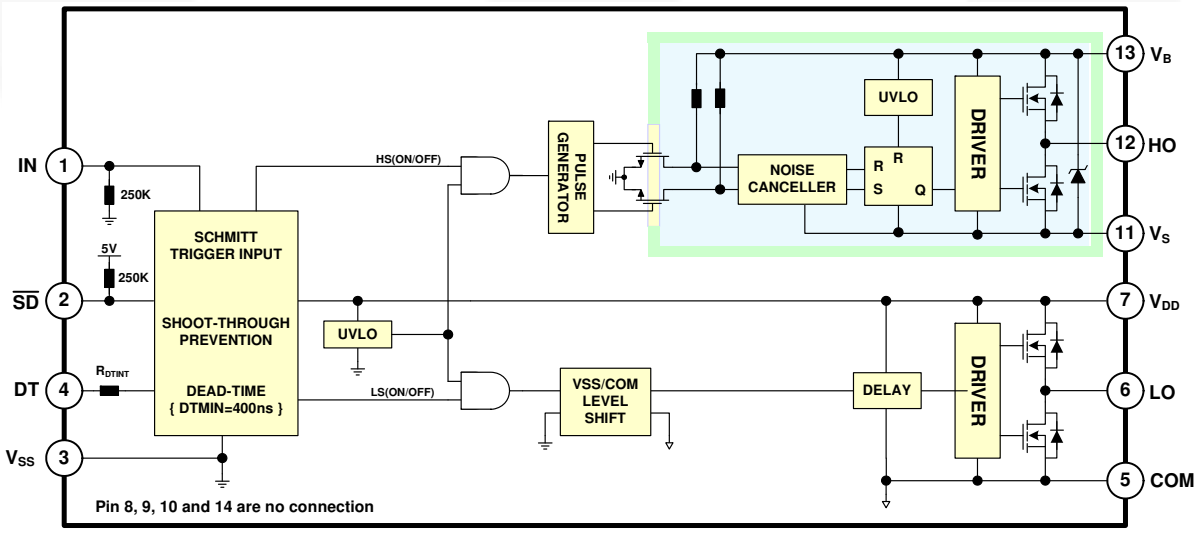


Figure 2. Functional Block Diagram

Pin Configuration

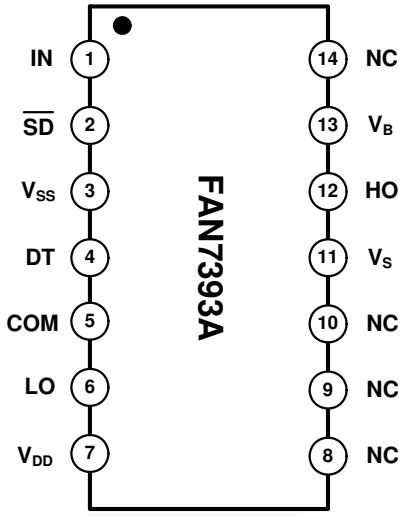


Figure 3. Pin Configurations (Top View)

Pin Definitions

Pin #	Name	Description
1	IN	Logic Input for High-Side and Low-Side Gate Driver Output, In-Phase with HO
2	$\overline{SD}$	Logic Input for Shutdown
3	V_{SS}	Logic Ground
4	DT	Dead-Time Control with External Resistor (Referenced to V_{SS})
5	COM	Ground
6	LO	Low-Side Driver Return
7	V_{DD}	Supply Voltage
8	NC	No Connection
9	NC	No Connection
10	NC	No Connection
11	V_S	High-Voltage Floating Supply Return
12	HO	High-Side Driver Output
13	V_B	High-Side Floating Supply
14	NC	No Connection

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. T_A=25°C unless otherwise specified.

Symbol	Characteristics	Min.	Max.	Unit
V_B	High-Side Floating Supply Voltage	-0.3	625.0	V
V_S	High-Side Floating Offset Voltage(1)	V_B-V_{SHUNT}	V_B+0.3	V
V_{HO}	High-Side Floating Output Voltage	V_S-0.3	V_B+0.3	V
V_{LO}	Low-Side Output Voltage	-0.3	V_{DD}+0.3	V
V_{DD}	Low-Side and Logic Fixed Supply Voltage	-0.3	25.0	V
V_{IN}	Logic Input Voltage (IN)	-0.3	V_{DD}+0.3	V
V_{SD}	Logic Input Voltage ($\overline{SD}$)	V_{SS}	5.5	V
DT	Programmable Dead-Time Pin Voltage	-0.3	V_{DD}+0.3	V
V_{SS}	Logic Ground	V_{DD}-25	V_{DD}+0.3	V
dV_S/dt	Allowable Offset Voltage Slew Rate		± 50	V/ns
P_D	Power Dissipation(2, 3, 4)		1	W
θ_{JA}	Thermal Resistance		110	°C/W
T_J	Junction Temperature		+150	°C
T_{STG}	Storage Temperature	-55	+150	°C

Notes:

1. This IC contains a shunt regulator on V_{BS}. This supply pin should not be driven by a low-impedance voltage source greater than V_{SHUNT} specified in the Electrical Characteristics section.
2. Mounted on 76.2 x 114.3 x 1.6mm PCB (FR-4 glass epoxy material).
3. Refer to the following standards:
   JESD51-2: Integral circuits thermal test method environmental conditions - natural convection, and
   JESD51-3: Low effective thermal conductivity test board for leaded surface mount packages.
4. Do not exceed maximum P_D under any circumstances.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Min.	Max.	Unit
V_B	High-Side Floating Supply Voltage	V_S+10	V_S+20	V
V_S	High-Side Floating Supply Offset Voltage	6-V_{DD}	600	V
V_{HO}	High-Side Output Voltage	V_S	V_B	V
V_{DD}	Low-Side and Logic Fixed Supply Voltage	10	20	V
V_{LO}	Low-Side Output Voltage	COM	V_{DD}	V
V_{IN}	Logic Input Voltage (IN)	V_{SS}	V_{DD}	V
V_{SD}	Logic Input Voltage ($\overline{SD}$)	V_{SS}	5	V
DT	Programmable Dead-Time Pin Voltage	V_{SS}	V_{DD}	V
V_{SS}	Logic Ground	-5	+5	V
T_A	Operating Ambient Temperature	-40	+125	°C

Electrical Characteristics

$V_{BIAS}(V_{DD}, V_{BS})$=15.0V, V_{SS}=COM=0V, DT=V_{SS}, and T_A=25°C unless otherwise specified. The V_{IN} and I_{IN} parameters are referenced to V_{SS}/COM and are applicable to the respective input leads: IN and $\overline{SD}$. The V_O and I_O parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Characteristics	Test Condition	Min.	Typ.	Max.	Unit
POWER SUPPLY SECTION						
I_{QDD}	Quiescent V_{DD} Supply Current	V_{IN}=0V or 5V		600	1000	μA
I_{QBS}	Quiescent V_{BS} Supply Current	V_{IN}=0V or 5V		55	100	μA
I_{PDD}	Operating V_{DD} Supply Current	f_{IN}=20KHz, No Load		1.0	1.6	mA
I_{PBS}	Operating V_{BS} Supply Current	C_L=1nF, f_{IN}=20KHz, RMS		450	800	μA
I_{SD}	Shutdown Mode Supply Current	$\overline{SD}$=V_{SS}		650	1000	μA
I_{LK}	Offset Supply Leakage Current	V_B=V_S=600V			10	μA
BOOTSTRAPPED SUPPLY SECTION						
V_{DDUV+} V_{BSUV+}	V_{DD} and V_{BS} Supply Under-Voltage Positive-Going Threshold Voltage	V_{IN}=0V, V_{DD}=V_{BS}=Sweep	7.8	8.8	9.8	V
V_{DDUV-} V_{BSUV-}	V_{DD} and V_{BS} Supply Under-Voltage Negative-Going Threshold Voltage	V_{IN}=0V, V_{DD}=V_{BS}=Sweep	7.3	8.3	9.3	V
V_{DDUVH-} V_{BSUVH}	V_{DD} and V_{BS} Supply Under-Voltage Lockout Hysteresis Voltage	V_{IN}=0V, V_{DD}=V_{BS}=Sweep		0.5		V
SHUNT REGULATOR SECTION						
V_{SHUNT}	Shunt Regulator Clamping Voltage for V_{BS}	V_{BS}=Sweep, I_{SHUNT}=5mA	21	23	25	V
INPUT LOGIC SECTION						
V_{IH}	Logic “1” Input Voltage for HO & Logic “0” for LO		2.5			V
V_{IL}	Logic “0” Input Voltage for HO & Logic “1” for LO				0.8	V
I_{IN+}	Logic Input High Bias Current	V_{IN}=5V, $\overline{SD}$=0V		20	50	μA
I_{IN-}	Logic Input Low Bias Current	V_{IN}=0V, $\overline{SD}$=5V			3	μA
R_{IN}	Logic Input Pull-Down Resistance		100	250		KΩ
$V_{SDCLAMP}$	Shutdown ($\overline{SD}$) Input Clamping Voltage(5)			5.0	5.5	V
$\overline{SD}$+	Shutdown ($\overline{SD}$) Input Positive-Going Threshold		2.5			V
$\overline{SD}$-	Shutdown ($\overline{SD}$) Input Negative-Going Threshold				0.8	V
R_{PSD}	Shutdown ($\overline{SD}$) Input Pull-Up Resistance		100	250		KΩ
GATE DRIVER OUTPUT SECTION						
V_{OH}	High-Level Output Voltage (V_{BIAS} - V_O)	No Load (I_O=0A)			1.5	V
V_{OL}	Low-Level Output Voltage	No Load (I_O=0A)			100	mV
I_{O+}	Output High, Short-Circuit Pulsed Current(5)	V_{HO}=0V, V_{IN}=5V, PW ≤10μs	2.0	2.5		A
I_{O-}	Output Low, Short-Circuit Pulsed Current(5)	V_{HO}=15V, V_{IN}=0V, PW ≤10μs	2.0	2.5		A
V_{SS}/COM	V_{SS}-COM/COM-V_{SS} Voltage Endurability(5)		-5.0		5.0	V
V_S	Allowable Negative V_S Pin Voltage for IN Signal Propagation to HO			-9.8	-7.0	V

Note:

5 These parameters are guaranteed by design.

Dynamic Electrical Characteristics

V_{BIAS}(V_{DD}, V_{BS})=15.0V, V_{SS}=COM=0V, C_L=1000pF, DT=V_{SS}, and T_A=25°C, unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
t_{ON}	Turn-On Propagation Delay(6)	V_S=0V, R_{DT}=0Ω		530	730	ns
t_{OFF}	Turn-Off Propagation Delay	V_S=0V		130	250	ns
t_{SD}	Shutdown Propagation Delay			140	210	ns
Mt_{ON}	Delay Matching, HO and LO Turn-On			0	90	ns
Mt_{OFF}	Delay Matching, HO and LO Turn-Off			0	40	ns
t_R	Turn-On Rise Time	V_S=0V		25	50	ns
t_F	Turn-Off Fall Time	V_S=0V		15	35	ns
DT	Dead Time: LO Turn-Off to HO Turn-On, HO Turn-Off to LO Turn-On	R_{DT}=0Ω	300	400	500	ns
		R_{DT}=200KΩ	4	5	6	µs
MDT	Dead-Time Matching=|DT_{LO-HO} - DT_{HO-LO}|	R_{DT}=0Ω		0	40	ns
		R_{DT}=200KΩ		0	500	ns

Note:

6 The turn-on propagation delay includes dead time.

Typical Characteristics

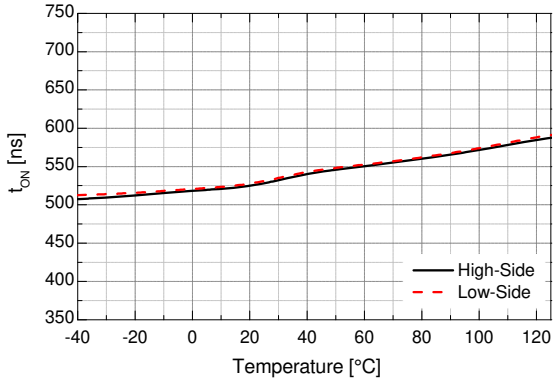


Figure 4. Turn-On Propagation Delay vs. Temperature

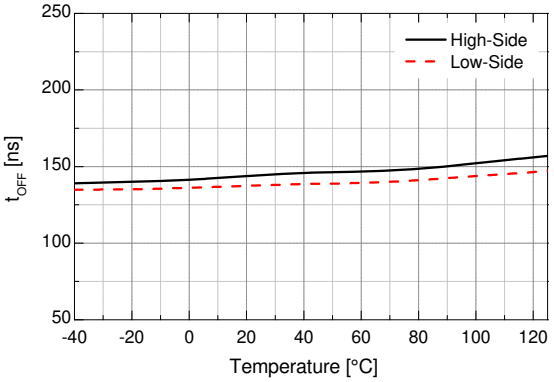


Figure 5. Turn-Off Propagation Delay vs. Temperature

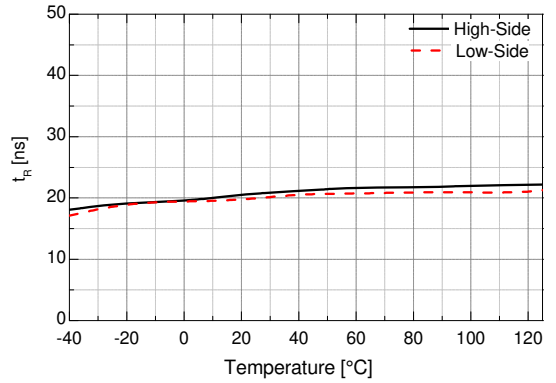


Figure 6. Turn-On Rise Time vs. Temperature

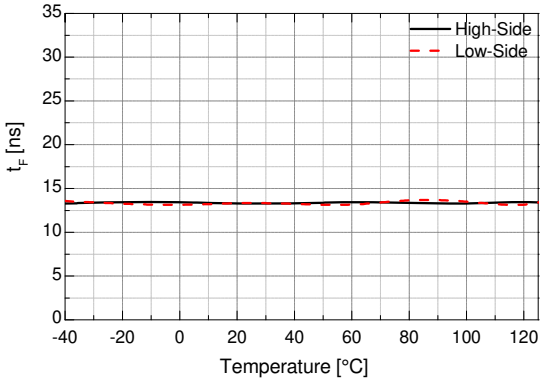


Figure 7. Turn-Off Fall Time vs. Temperature

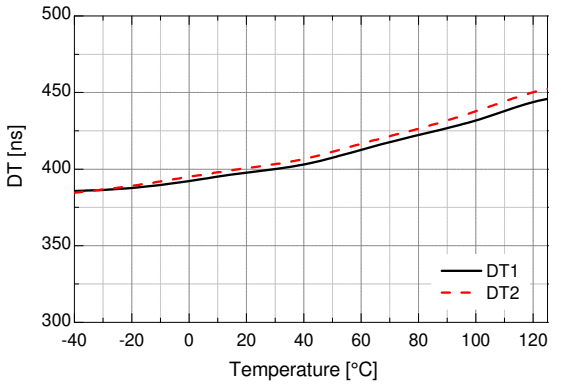


Figure 8. Dead Time (R_{DT}=0Ω) vs. Temperature

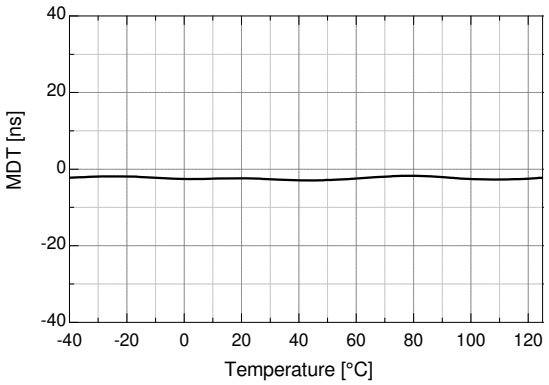


Figure 9. Dead Time Matching (R_{DT}=0Ω) vs. Temperature

Typical Characteristics (Continued)

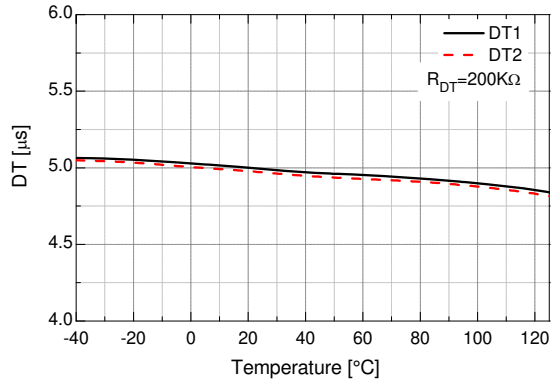


Figure 10. Dead Time (R_{DT}=200KΩ) vs. Temperature

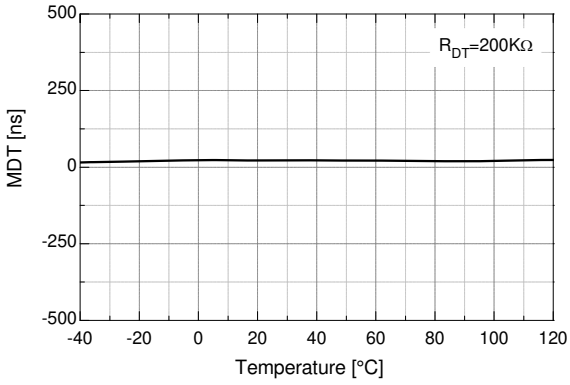


Figure 11. Dead-Time Matching (R_{DT}=200KΩ) vs. Temperature

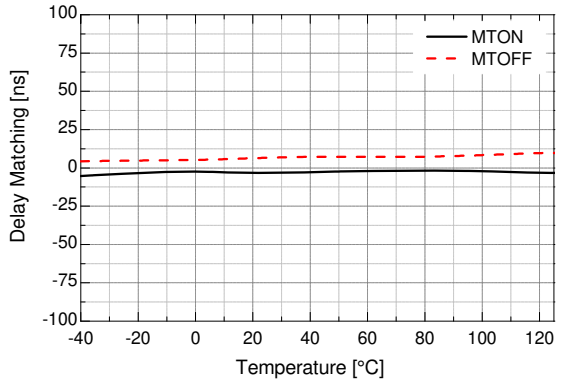


Figure 12. Delay Matching vs. Temperature

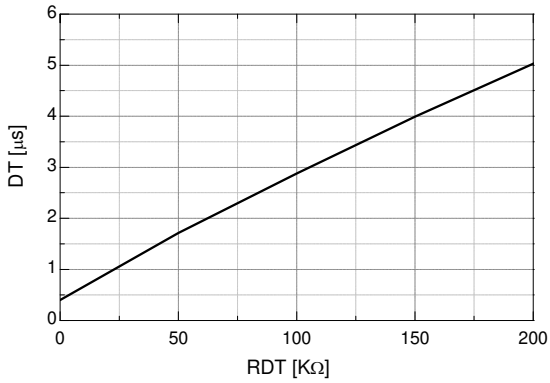


Figure 13. Dead Time vs. R_{DT}

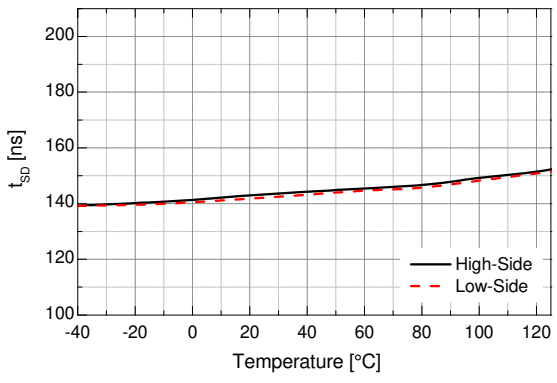


Figure 14. Shutdown Propagation Delay vs. Temperature

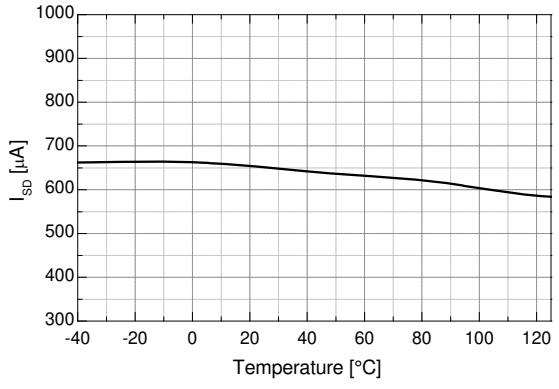


Figure 15. Shutdown Mode Supply Current vs. Temperature

Typical Characteristics (Continued)

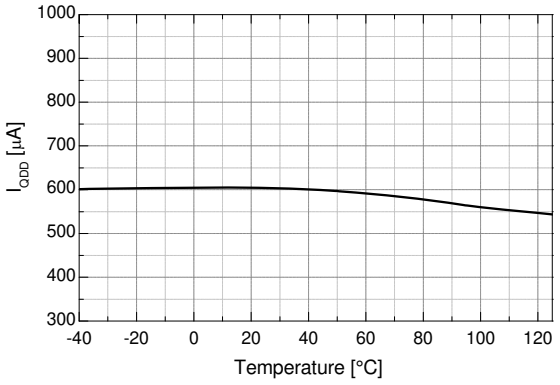


Figure 16. Quiescent V_{DD} Supply Current vs. Temperature

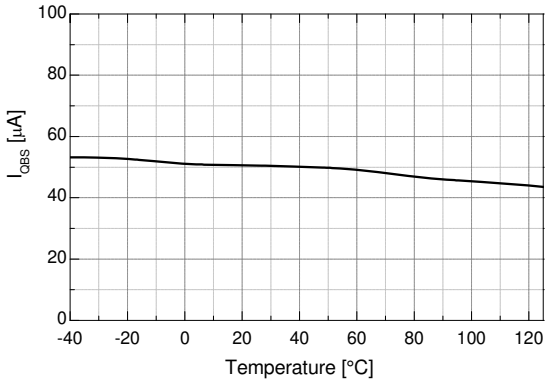


Figure 17. Quiescent V_{BS} Supply Current vs. Temperature

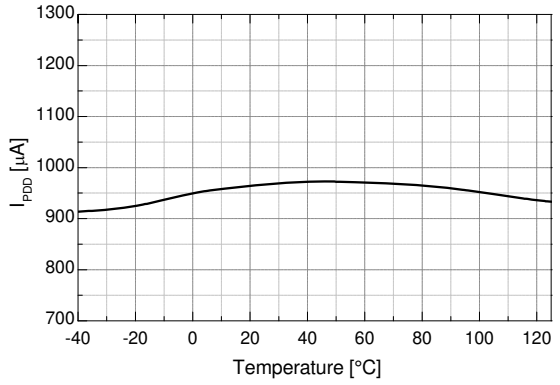


Figure 18. Operating V_{DD} Supply Current vs. Temperature

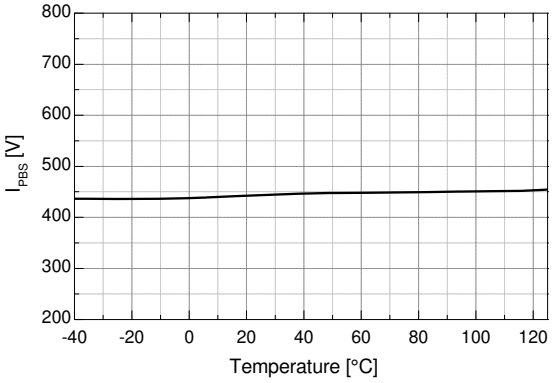


Figure 19. Operating V_{BS} Supply Current vs. Temperature

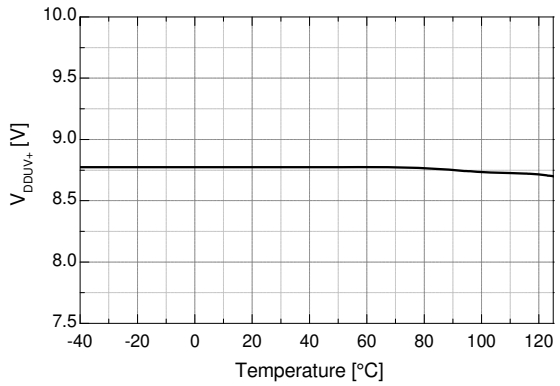


Figure 20. V_{DD} UVLO+ vs. Temperature

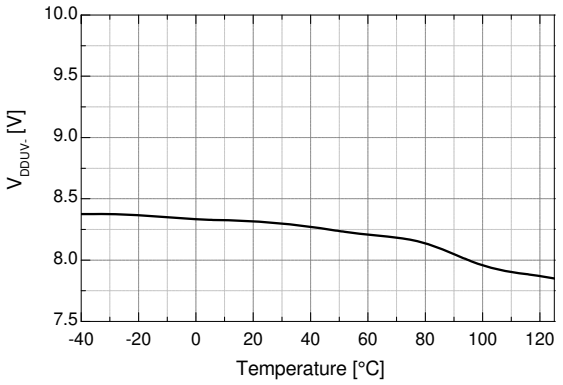


Figure 21. V_{DD} UVLO- vs. Temperature

Typical Characteristics (Continued)

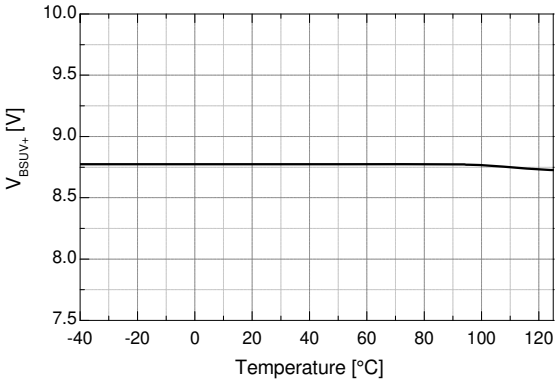


Figure 22. V_{BS} UVLO+ vs. Temperature

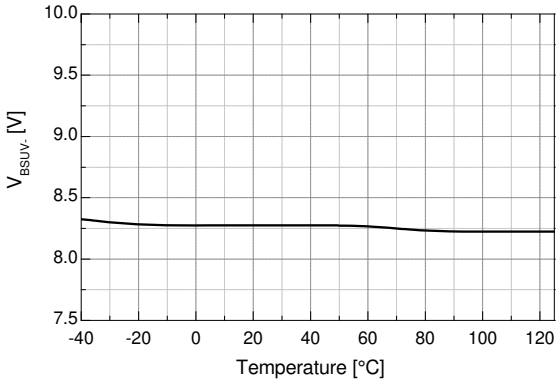


Figure 23. V_{BS} UVLO- vs. Temperature

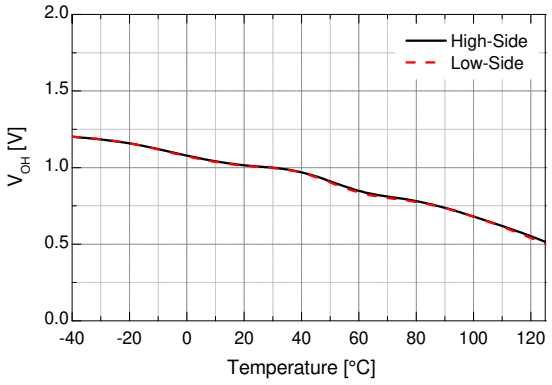


Figure 24. High-Level Output Voltage vs. Temperature

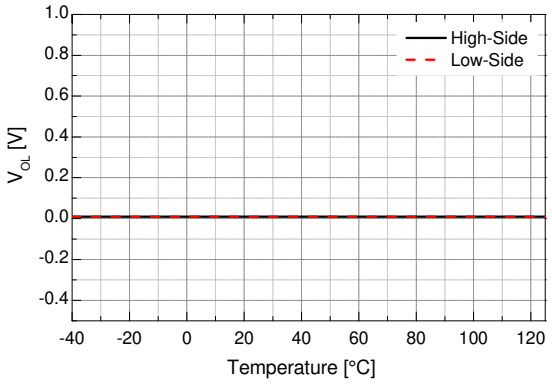


Figure 25. Low-Level Output Voltage vs. Temperature

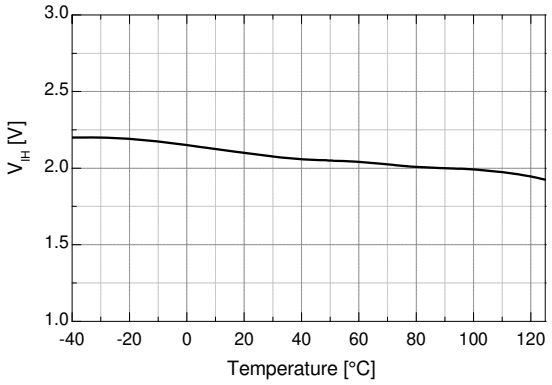


Figure 26. Logic HIGH Input Voltage vs. Temperature

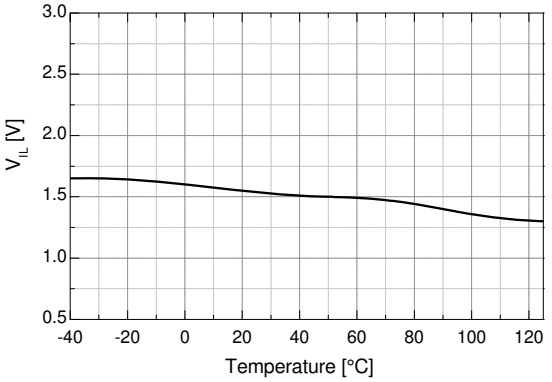


Figure 27. Logic LOW Input Voltage vs. Temperature

Typical Characteristics (Continued)

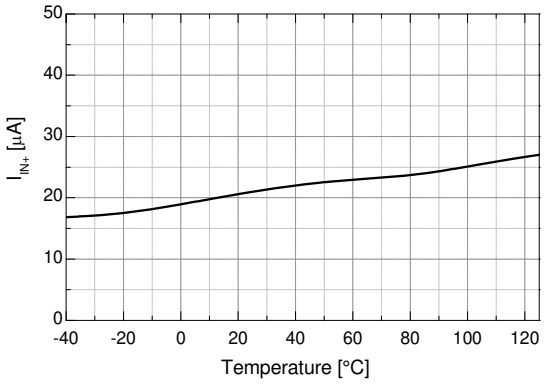


Figure 28. Logic Input High Bias Current vs. Temperature

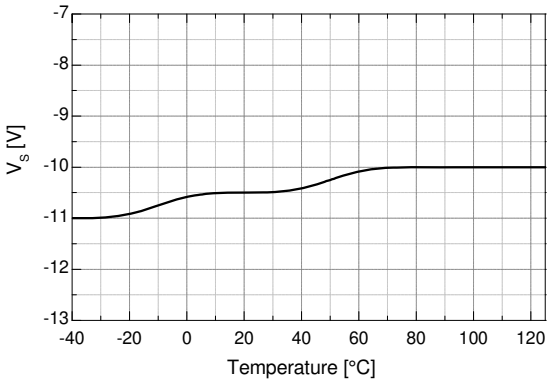


Figure 29. Allowable Negative V_S Voltage vs. Temperature

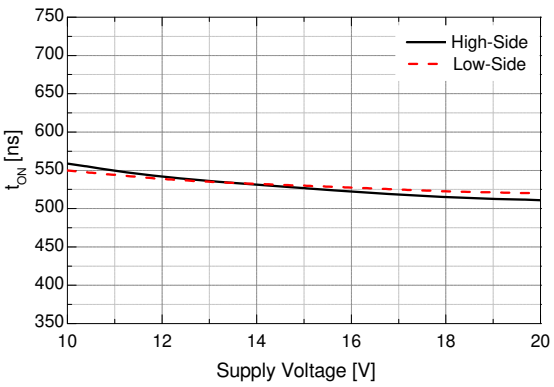


Figure 30. Turn-On Propagation Delay vs. Supply Voltage

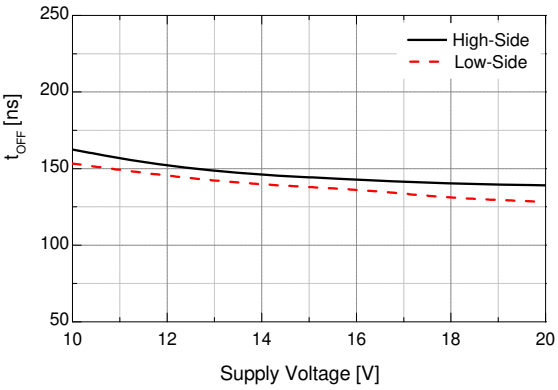


Figure 31. Turn-Off Propagation Delay vs. Supply Voltage

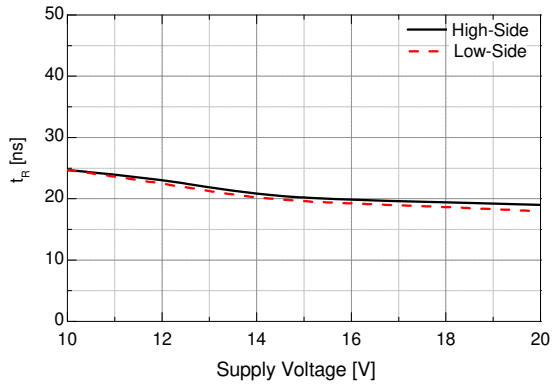


Figure 32. Turn-On Rise Time vs. Supply Voltage

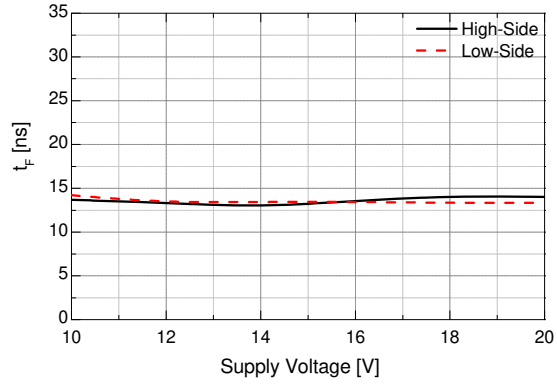


Figure 33. Turn-Off Fall Time vs. Supply Voltage

Typical Characteristics (Continued)

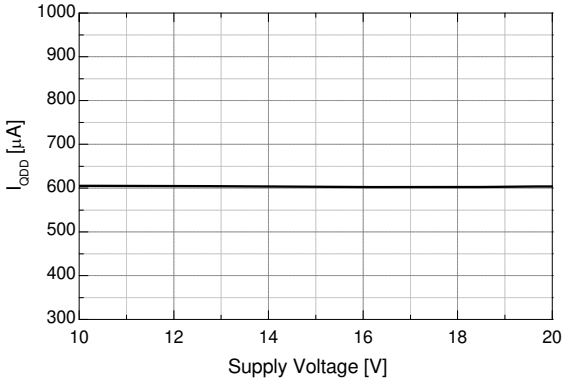


Figure 34. Quiescent V_{DD} Supply Current vs. Supply Voltage

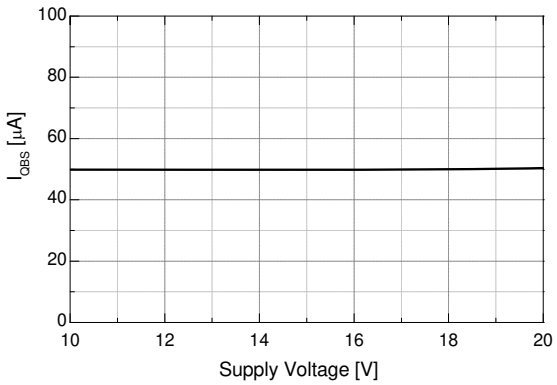


Figure 35. Quiescent V_{BS} Supply Current vs. Supply Voltage

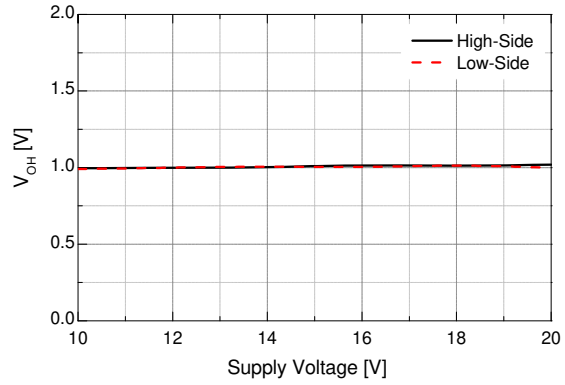


Figure 36. High-Level Output Voltage vs. Supply Voltage

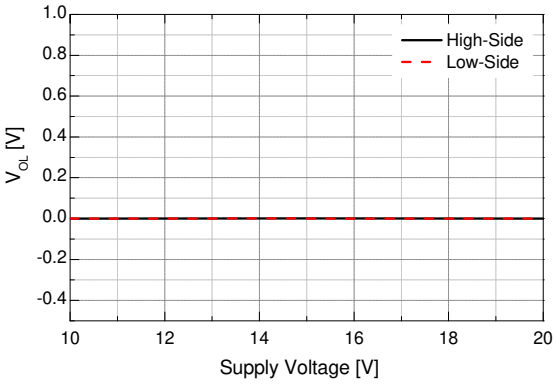


Figure 37. Low-Level Output Voltage vs. Supply Voltage

Switching Time Definitions

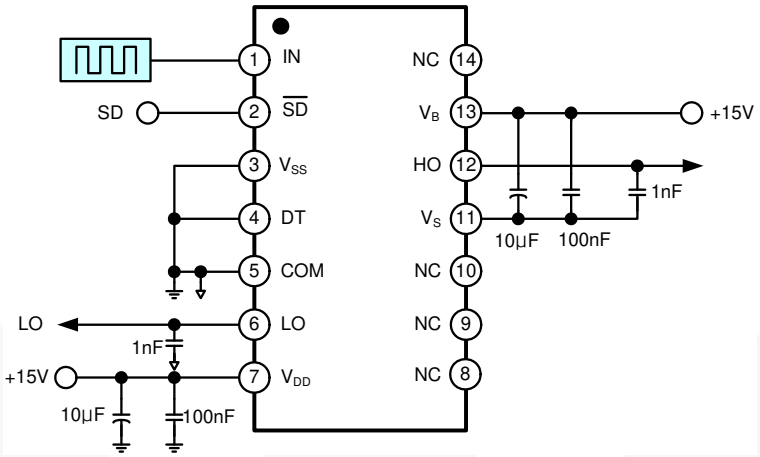


Figure 38. Switching Time Test Circuit

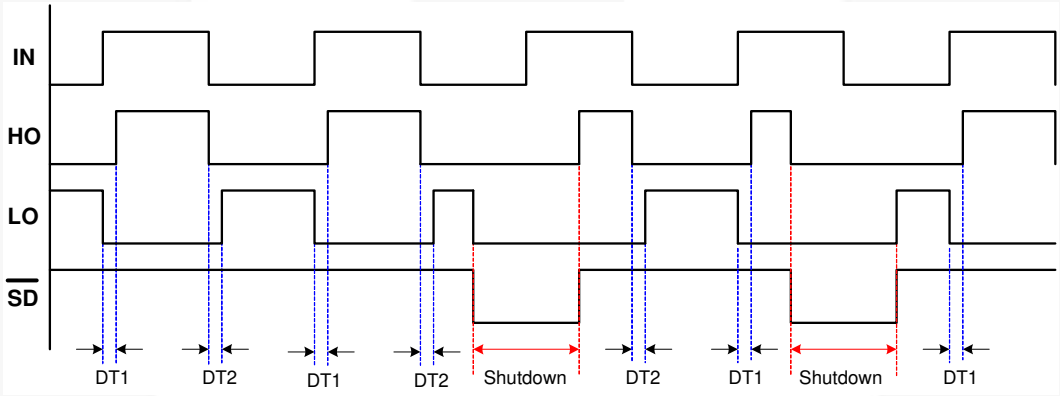


Figure 39. Input / Output Timing Diagram

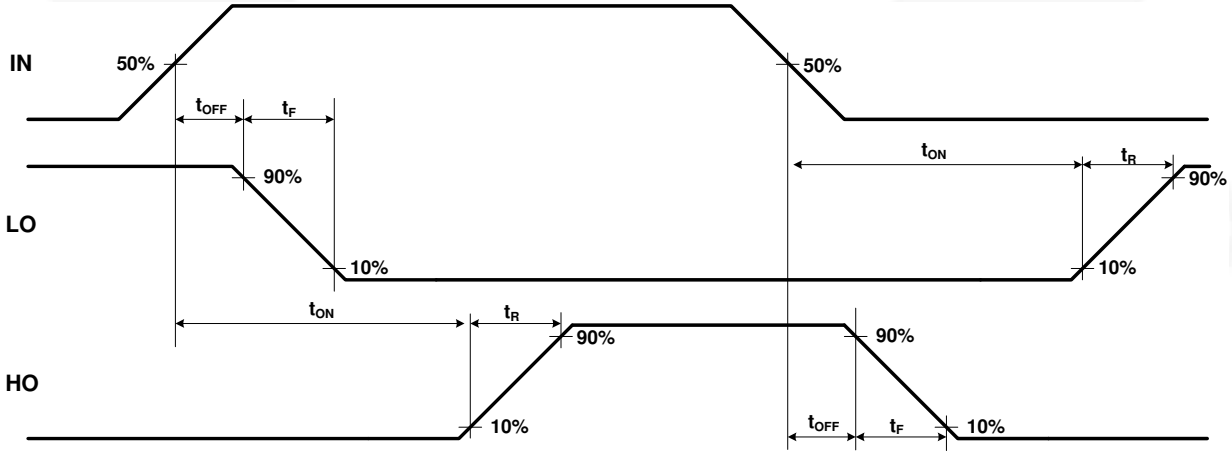


Figure 40. Switching Time Waveform Definition

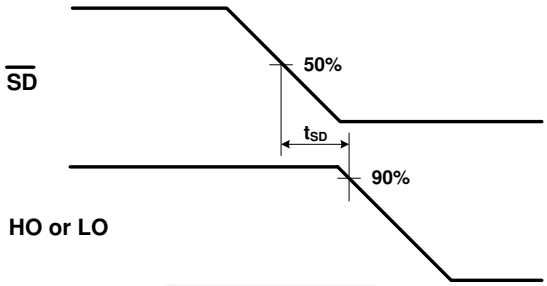
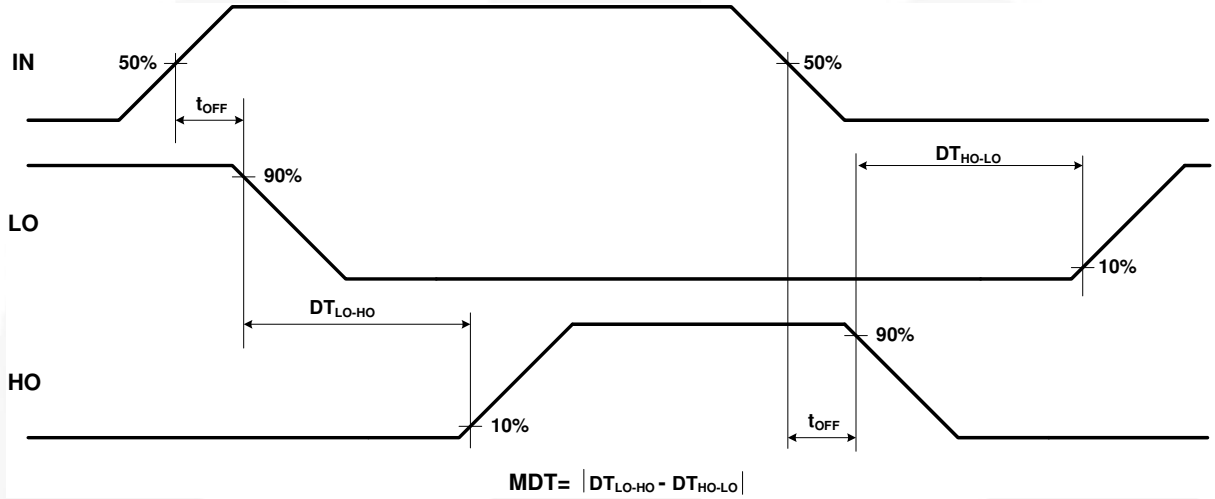


Figure 41. Shutdown Waveform Definition



$$MDT = |DT_{LO-HO} - DT_{HO-LO}|$$

Figure 42. Dead-Time Waveform Definition

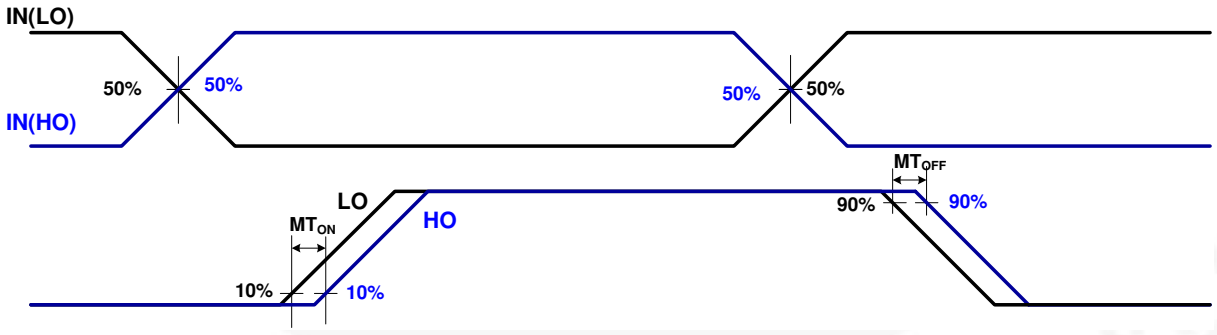
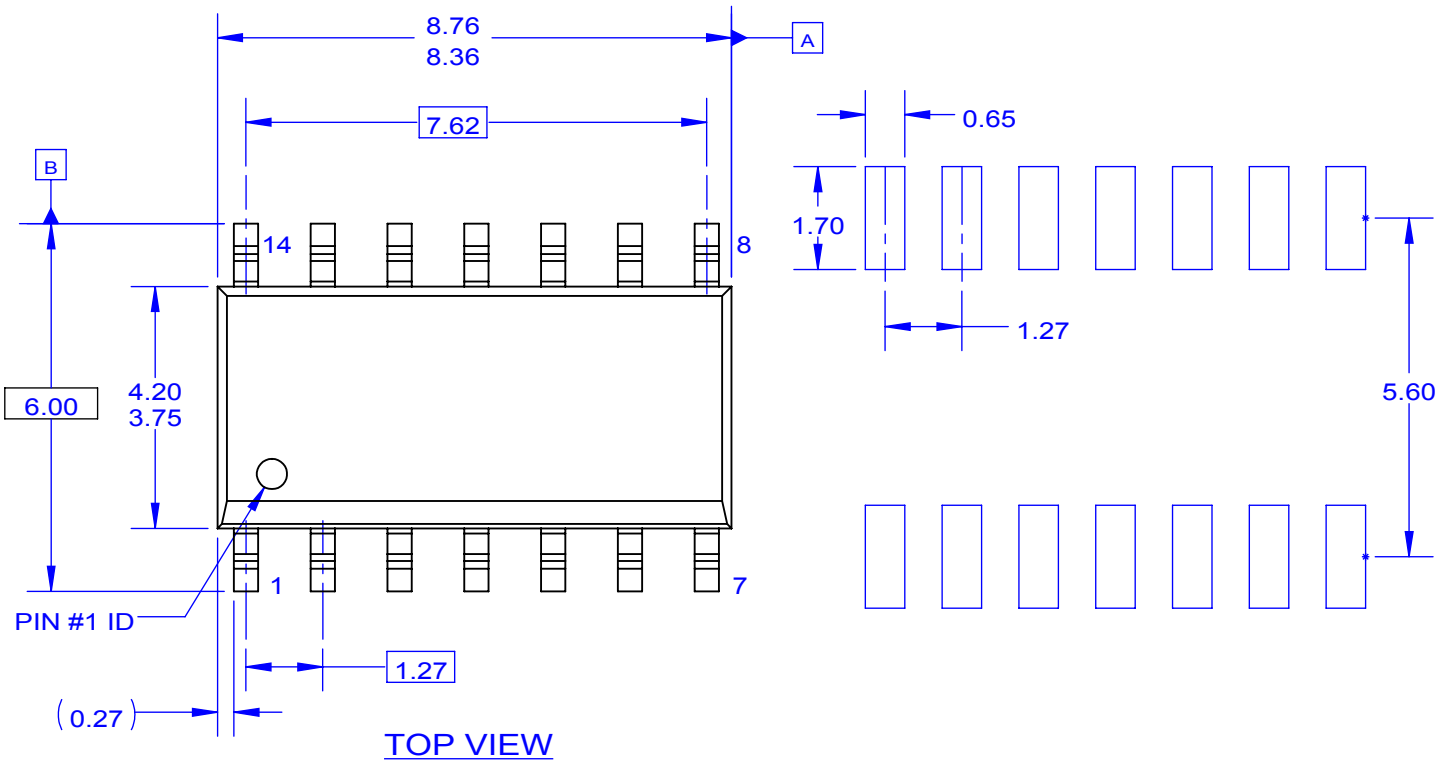
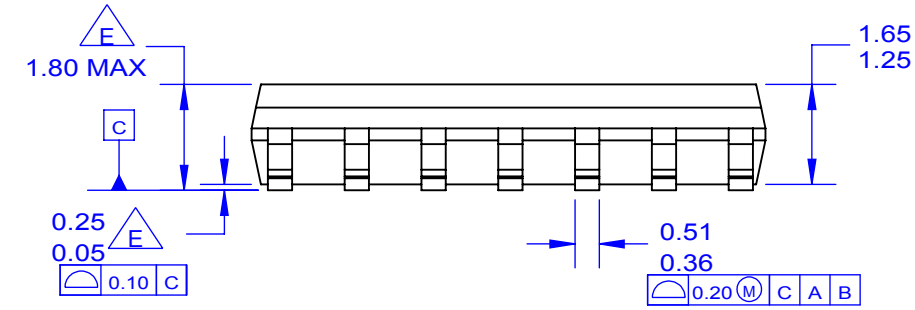


Figure 43. Delay Matching Waveform Definition

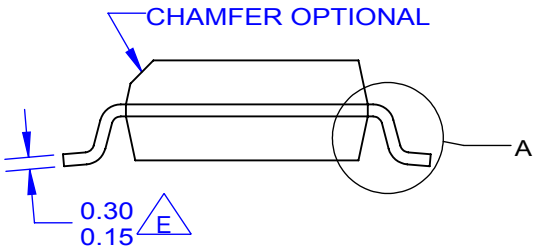


TOP VIEW



ALL LEAD TIPS

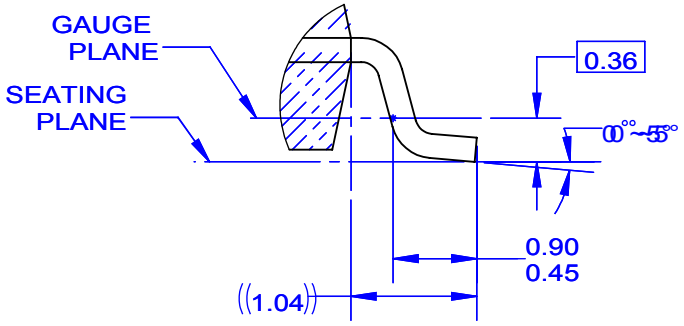
SIDE VIEW



END VIEW

NOTES: UNLESS OTHERWISE SPECIFIED

A. THIS PACKAGE REFERENCE TO JEDEC MS-012 VARIATION AB.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
D. DIMENSIONS AND TOLERANCES AS PER ASME Y14.5-1994.
E OUT OF JEDEC STANDARD VALUE.
F. LAND PATTERN STANDARD: SOIC127P600X145-14M.
G. FILE NAME: MKT-M14C REV2



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SCALE 2:1

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